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(71) Applicant *(for all designated States except US)*: **LAM RESEARCH CORPORATION** [US/US]; 4650 Cushing Parkway, Fremont, California 94538 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **HUANG, Tuochuan** [US/US]; 19689 Douglass Ln., Saratoga, California 95070 (US). **REN, Daxing** [CN/US]; 7373 Joshua Circle, Pleasanton, California 94588 (US). **SHIH, Hong** [US/US]; 19048 E. Garnet Way, Walnut, California 91789 (US). **ZHOU, Catherine** [CN/US]; 41915 Mckay Street, Fremont, California 94539 (US). **YAN, Chun** [US/US]; 6066 Elmbridge Drive, San Jose, California 95129 (US). **MAGNI, Enrico** [IT/US]; 3144 Cranwood Court, Pleasanton, California 94588 (US). **YEN, Bi, Ming** [—/US]; 40495 Carmelita Court, Fremont, California 94539 (US). **HUBACEK, Jerome** [US/US]; 644 Hobart Court, Fremont, California 94539 (US). **LIM, Dae, J.** [US/US]; 34555 Pueblo Terrace, Fremont, California 94555 (US). **SUNG, Dougyong** [KR/US]; 39639 Leslie Street, Apt #262, Fremont, California 94538 (US).

(74) Agent: **SKIFF, Peter, K.**; BUCHANAN INGERSOLL PC, Po Box 1404, Alexandria, Virginia 22313-1404 (US).

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(54) Title: METHODS FOR SILICON ELECTRODE ASSEMBLY ETCH RATE AND ETCH UNIFORMITY RECOVERY

(57) Abstract: Methods for cleaning an electrode assembly, which can be used for etching a dielectric material in a plasma etching chamber after the cleaning, comprise polishing a silicon surface of the electrode assembly, preferably to remove black silicon contamination therefrom.

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